

ABSTRACT OF THE DISCLOSURE

A dual damascene interconnect structure having a patterned multilayer of spun-on dielectrics on a substrate is provided. The structure
5 includes: a patterned multilayer of spun-on dielectrics on a substrate, including: a cap layer; a first non-porous via level low-k dielectric layer having thereon metal via conductors with a bottom portion and sidewalls; an etch stop layer; a first porous low-k line level dielectric layer having thereon metal line conductors with a bottom portion and sidewalls; a polish
10 stop layer over the first porous low-k dielectric; a second thin non-porous low-k dielectric layer for coating and planarizing the line and via sidewalls; and a liner material between the metal via and line conductors and the dielectric layers. Also provided is a method of forming the dual
damascene interconnect structure.

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